## WHAT IS CLAIMED IS:

1. A liquid crystal display device comprising:

a thin film transistor formed over a first substrate, the thin film transistor comprising an amorphous semiconductor layer, and a gate electrode adjacent to the amorphous semiconductor layer with a gate insulating film interposed therebetween;

a drain electrode electrically connected to the amorphous semiconductor layer;

a common electrode disposed adjacent to the drain electrode;

a second substrate opposed to the first substrate; and

a liquid crystal interposed between the first and the second substrates, wherein an electric field is applied to the liquid crystal substantially in parallel with a surface of the first substrate by the common electrode and the drain electrode,

wherein a transparent conductive material is provided over the second substrate.

- 2. A liquid crystal display device according to claim 1 wherein the first and the second substrates comprise a glass or a quartz substrate.
- 3. A liquid crystal display device according to claim 1 wherein the amorphous semiconductor layer comprises silicon.
- 4. A liquid crystal display device according to claim 1 wherein the amorphous semiconductor layer is formed over the gate electrode.
- 5. A liquid crystal display device according to claim 1 wherein the gate electrode and the common electrode are formed on a same layer.
- 6. A liquid crystal display device according to claim 1 wherein the transparent conductive material functions as an electrode.

- 7. A liquid crystal display device according to claim 1 wherein each of the gate electrode and the common electrode has a curved surface.
  - 8. A liquid crystal display device comprising:

a thin film transistor formed over a first substrate, the thin film transistor comprising an amorphous semiconductor layer, and a gate electrode adjacent to the amorphous semiconductor layer with a gate insulating film interposed therebetween:

a drain electrode electrically connected to the amorphous semiconductor layer; a common electrode disposed adjacent to the drain electrode;

a second substrate opposed to the first substrate; and

a liquid crystal interposed between the first and the second substrates, wherein an electric field is applied to the liquid crystal substantially in parallel with a surface of the first substrate by the common electrode and the drain electrode,

wherein a transparent conductive material is provided over an entire surface of the second substrate.

- 9. A liquid crystal display device according to claim 8 wherein the first and the second substrates comprise a glass or a quartz substrate.
- 10. A liquid crystal display device according to claim 8 wherein the amorphous semiconductor layer comprises silicon.
- 11. A liquid crystal display device according to claim 8 wherein the amorphous semiconductor layer is formed over the gate electrode.
- 12. A liquid crystal display device according to claim 8 wherein the gate electrode and the common electrode are formed on a same layer.
- 13. A liquid crystal display device according to claim 8 wherein the transparent conductive material functions as an electrode.

- 14. A liquid crystal display device according to claim 8 wherein each of the gate electrode and the common electrode has a curved surface.
  - 15. A liquid crystal display device comprising:

a thin film transistor formed over a first substrate, the thin film transistor comprising an amorphous semiconductor layer, and a gate electrode adjacent to the amorphous semiconductor layer with a gate insulating film interposed therebetween;

a drain electrode electrically connected to the amorphous semiconductor layer; a common electrode disposed adjacent to the drain electrode;

a second substrate opposed to the first substrate; and

a liquid crystal interposed between the first and the second substrates, wherein an electric field is applied to the liquid crystal substantially in parallel with a surface of the first substrate by the common electrode and the drain electrode,

wherein a transparent conductive material is provided over a portion of the second substrate.

- 16. A liquid crystal display device according to claim 15 wherein the first and the second substrates comprise a glass or a quartz substrate.
- 17. A liquid crystal display device according to claim 15 wherein the amorphous semiconductor layer comprises silicon.
- 18. A liquid crystal display device according to claim 15 wherein the amorphous semiconductor layer is formed over the gate electrode.
- 19. A liquid crystal display device according to claim 15 wherein the gate electrode and the common electrode are formed on a same layer.
- 20. A liquid crystal display device according to claim 15 wherein the transparent conductive material functions as an electrode.

- 21. A liquid crystal display device according to claim 15 wherein each of the gate electrode and the common electrode has a curved surface.
  - 22. A liquid crystal display device comprising:

a thin film transistor formed over a first substrate, the thin film transistor comprising an amorphous semiconductor layer, and a gate electrode adjacent to the amorphous semiconductor layer with a gate insulating film interposed therebetween:

a drain electrode electrically connected to the amorphous semiconductor layer; a common electrode disposed adjacent to the drain electrode;

a second substrate opposed to the first substrate; and

a liquid crystal interposed between the first and the second substrates, wherein an electric field is applied to the liquid crystal substantially in parallel with a surface of the first substrate by the common electrode and the drain electrode,

wherein a transparent conductive material comprising indium tin oxide is provided over the second substrate.

- 23. A liquid crystal display device according to claim 22 wherein the first and the second substrates comprise a glass or a quartz substrate.
- 24. A liquid crystal display device according to claim 22 wherein the amorphous semiconductor layer comprises silicon.
- 25. A liquid crystal display device according to claim 22 wherein the amorphous semiconductor layer is formed over the gate electrode.
- 26. A liquid crystal display device according to claim 22 wherein the gate electrode and the common electrode are formed on a same layer.
- 27. A liquid crystal display device according to claim 22 wherein the transparent conductive material functions as an electrode.

- 28. A liquid crystal display device according to claim 22 wherein each of the gate electrode and the common electrode has a curved surface.
  - 29. A liquid crystal display device comprising:

a thin film transistor formed over a first substrate, the thin film transistor comprising an amorphous semiconductor layer, and a gate electrode adjacent to the amorphous semiconductor layer with a gate insulating film interposed therebetween;

a drain electrode electrically connected to the amorphous semiconductor layer;

a common electrode disposed adjacent to the drain electrode;

a second substrate opposed to the first substrate; and

a liquid crystal interposed between the first and the second substrates, wherein an electric field is applied to the liquid crystal substantially in parallel with a surface of the first substrate by the common electrode and the drain electrode,

wherein a transparent conductive material comprising indium tin oxide is provided over an entire surface of the second substrate.

- 30. A liquid crystal display device according to claim 29 wherein the first and the second substrates comprise a glass or a quartz substrate.
- 31. A liquid crystal display device according to claim 29 wherein the amorphous semiconductor layer comprises silicon.
- 32. A liquid crystal display device according to claim 29 wherein the amorphous semiconductor layer is formed over the gate electrode.
- 33. A liquid crystal display device according to claim 29 wherein the gate electrode and the common electrode are formed on a same layer.
- 34. A liquid crystal display device according to claim 29 wherein the transparent conductive material functions as an electrode.

- 35. A liquid crystal display device according to claim 29 wherein each of the gate electrode and the common electrode has a curved surface.
  - 36. A liquid crystal display device comprising:

a thin film transistor formed over a first substrate, the thin film transistor comprising an amorphous semiconductor layer, and a gate electrode adjacent to the amorphous semiconductor layer with a gate insulating film interposed therebetween;

a drain electrode electrically connected to the amorphous semiconductor layer; a common electrode disposed adjacent to the drain electrode;

a second substrate opposed to the first substrate; and

a liquid crystal interposed between the first and the second substrates, wherein an electric field is applied to the liquid crystal substantially in parallel with a surface of the first substrate by the common electrode and the drain electrode,

wherein a transparent conductive material comprising indium tin oxide is provided over a portion of the second substrate.

- 37. A liquid crystal display device according to claim 36 wherein the first and the second substrates comprise a glass or a quartz substrate.
- 38. A liquid crystal display device according to claim 36 wherein the amorphous semiconductor layer comprises silicon.
- 39. A liquid crystal display device according to claim 36 wherein the amorphous semiconductor layer is formed over the gate electrode.
- 40. A liquid crystal display device according to claim 36 wherein the gate electrode and the common electrode are formed on a same layer.
- 41. A liquid crystal display device according to claim 36 wherein the transparent conductive material functions as an electrode.

42. A liquid crystal display device according to claim 36 wherein each of the gate electrode and the common electrode has a curved surface.

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